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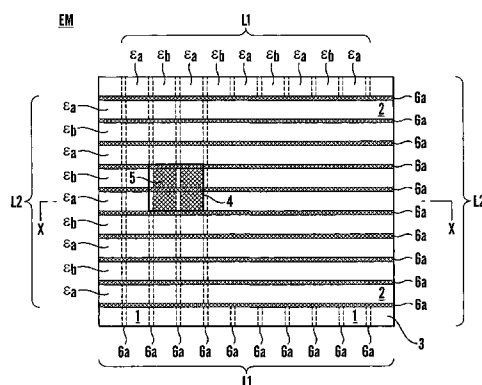
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(54) Title: ELECTRODES, METHOD AND APPARATUS FOR MEMORY STRUCTURE



(57) Abstract: In an electrode means comprising a first and a second thin-film electrode layers (L1, L2) with electrodes (e) in the form of parallel strip-like electrical conductors in each layer, the electrodes (e) are provided only separated by a thin film (6) of an electrically insulating material with a thickness at most a fraction of the width of the electrodes and at least extending along the side edges thereof and forming an insulating wall (6a) therebetween. The electrode layers (L1, L2) are planarized to obtain an extremely planar surface. In an apparatus comprising one or more electrode means (EM), the electrode layers (L1, L2) of each are mutually oriented with their respective electrodes (1;2) crossing at an angle, preferably orthogonally and with a functional medium (3) provided globally in sandwich therebetween, such that a preferably passive matrix-addressable apparatus is obtained and suited for use as e.g. a matrix-addressable data processing device or matrix-addressable data storage device comprising individually addressable functional elements (5) in the form of e.g. respectively logic cells or memory cells, the fill factor thereof in the global functional medium (3) approaching unity and a maximum number of the cells in the apparatus of approximately A/f^2 , wherein A is the area of the global functional medium (3) sandwiched between the electrode layers (L1, L2), and f is a process-constrained minimum feature.



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